

Product Overview

NTS2101P: Small Signal MOSFET -8V -1.4A 100 mOhm Single P-Channel SC-70

For complete documentation, see the data sheet.

This is an 8.0 V P-Channel Power MOSFET.

Features

- Leading Trench Technology for Low RDS(on) Extending Battery Life
- -1.8 V Rated for Low Voltage Gate Drive
- SC-70 Surface Mount for Small Footprint (2x2 mm)

Applications

- High Side Load Switch
- Charging Circuit
- Single Cell Battery Application Applications

End Products

- Cell Phones
- Digital Cameras
- PDAs

Part Electrical Specifications

Product	Compliance	Status	Chan- nel Polar- ity	Confi- gura- tion	V _{SS} ^{(BR)D} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Pack- age Type
NTS2101PT1G	Pb-free Halide free	Active	P- Chan- nel	Singl- e	-8	8	-	1.4	0.29	78	65	-	6.4	6.4	640	SC- 70-3 / SOT- 323-3

For more information please contact your local sales support at www.onsemi.com.

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